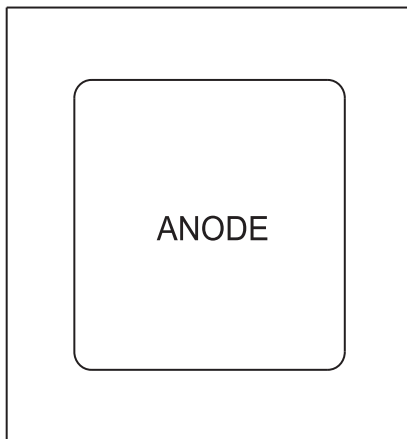


**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	18 X 18 MILS
Die Thickness	7.5 MILS
Anode Bonding Pad Area	11 X 11 MILS
Top Side Metalization	Al - 13,000Å TYP
Back Side Metalization	Au - 14,000Å TYP

**GEOMETRY**



BACKSIDE CATHODE R0

**GROSS DIE PER 4 INCH WAFER**

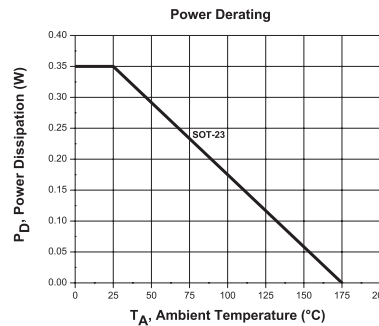
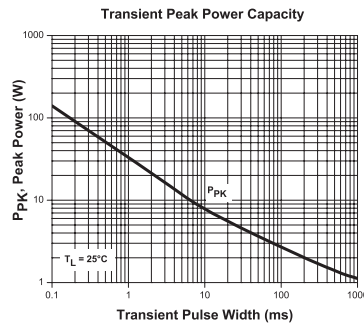
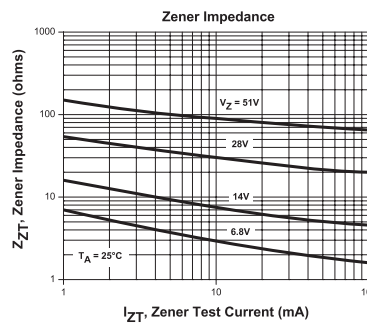
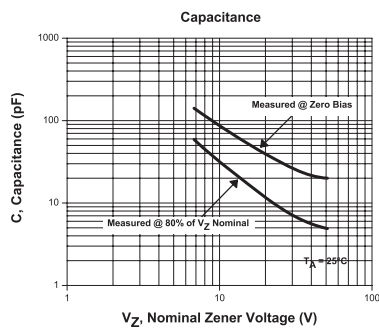
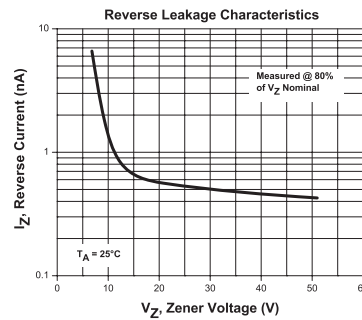
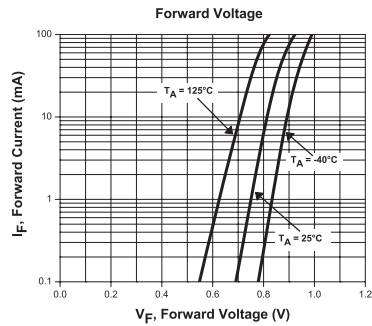
36,600

**PRINCIPAL DEVICE TYPES**

CMPZ5235B  
THRU  
CMPZ5261B

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
www.centalsemi.com

R4 (22-April 2008)



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Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
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